L Number	Hits		DB	Time stamp
22	13656	second near3 ((gate or scan\$4) and insulat\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/10 11:19
23	16	((((((insulat\$4 near8 (dielectric and silicon near3 nitride)) and ((gate or scan\$4) near8 ((chrom\$4 or cr) or (aluminum or al) or (molybdenum or mo) or (silver or ag))) and (((thin near3 film near3 transistor) or (tft)) and substrate) and ((drain or data or source or signal\$4) near3 (line or electrode))) and (passivation near3 (film or layer or plate or coat\$4))) and ((dielectric or permittiv\$4) near3 (constant or coefficient))) and 349/\$6) and (second near3 ((gate or scan\$4) and insulat\$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/10 11:20
24	7610	(second near3 insulat\$4) same (nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/10 11:20
25	8	((((((insulat\$4 near8 (dielectric and silicon near3 nitride)) and ((gate or scan\$4) near8 ((chrom\$4 or cr) or (aluminum or al) or (molybdenum or mo) or (silver or ag))) and (((thin near3 film near3 transistor) or (tft)) and substrate) and ((drain or data or source or signal\$4) near3 (line or electrode))) and (passivation near3 (film or layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/10 11:21
		or plate or coat\$4))) and ((dielectric or permittiv\$4) near3 (constant or coefficient))) and 349/\$6) and ((second near3 insulat\$4) same (nitride))		
26	12	"a-si:c:o" or "a-si:o:f"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/10 11:26
27	3	("a-si:c:o" or "a-si:o:f") and 349/\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/10 11:26
-	34614	349/\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/24 08:42
	1645	((thin near3 film near "3" transistor) or (tft)) and substrate and ((signal or gate or signaling) near3 (line or electrode)) and array and insulat\$4 and dielectric and (pixel near4 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 08:53
	811	349/\$6 and (((thin near3 film near "3" transistor) or (tft)) and substrate and ((signal or gate or signaling) near3 (line or electrode)) and array and insulat\$4 and dielectric and (pixel near4 electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/24 08:45
-	113819	silicon near3 nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 09:22

_	1380	((thin near3 film near "3" transistor) or (tft)) and substrate and ((signal or data or signaling) near3	USPAT; US-PGPUB;	2003/11/24 08:46
		(line or electrode)) and array and insulat\$4 and	EPO; JPO;	
		dielectric and (pixel near4 electrode)	DERWENT;	
		dicidente una (pixer ricura dicentracy	IBM_TDB	
· -	1708	((thin near3 film near3 transistor) or (tft)) and	USPAT;	2004/03/09 09:20
	17.00	substrate and ((signal or gate or signaling) near3	US-PGPUB;	
		(line or electrode)) and array and insulat\$4 and	EPO; JPO;	
		dielectric and (pixel near4 electrode)	DERWENT;	
		,	IBM_TDB	
-	1728	((thin near3 film near3 transistor) or (tft)) and	USPAT;	2004/03/09 09:20
		substrate and ((signal or gate or signaling or	US-PGPUB;	
		scan\$4 or data) near3 (line or electrode)) and	EPO; JPO;	
		array and insulat\$4 and dielectric and (pixel near4	DERWENT;	
		electrode)	IBM_TDB	
-	576		USPAT;	2004/03/09 09:21
		array near8 substrate) and ((signal or gate or	US-PGPUB;	
		signaling or scan\$4 or data) near3 (line or	EPO; JPO;	
		electrode)) and array and insulat\$4 and dielectric	DERWENT;	
	110	and (pixel near4 electrode)	IBM_TDB	2004/02/20 44 24
-	418	(((thin near3 film near3 transistor) or (tft)) near8	USPAT;	2004/03/09 11:01
		array near8 substrate) and ((signal or gate or	US-PGPUB;	
		signaling or scan\$4 or data) near3 (line or electrode)) and array and insulat\$4 and (dielectric	EPO; JPO; DERWENT;	
		near "6" constant) and (pixel near4 electrode) and	IBM_TDB	
		hole	1014-100	
_	118878	silicon near3 nitride	USPAT;	2004/03/09 09:23
	110070	sincon nears menae	US-PGPUB;	2004/03/03/03/03.23
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	295	((((thin near3 film near3 transistor) or (tft)) near8	USPAT;	2004/03/09 09:23
		array near8 substrate) and ((signal or gate or	US-PGPUB;	
		signaling or scan\$4 or data) near3 (line or	EPO; JPO;	
		electrode)) and array and insulat\$4 and (dielectric	DERWENT;	
		near "6" constant) and (pixel near4 electrode) and	IBM_TDB	
		hole) and (silicon near3 nitride)		l
-	241750	(indium near3 (tin or zinc) near3 oxide) or ito or	USPAT;	2004/03/09 09:24
		izo	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	226200	(indium adi (tin or zina) adi avida) az ita az iza	IBM_TDB	2004/02/00 00:24
-	236208	(indium adj (tin or zinc) adj oxide) or ito or izo	USPAT; US-PGPUB;	2004/03/09 09:24
			EPO; JPO;	
			DERWENT;	
]		IBM_TDB	
_	277	(((((thin near3 film near3 transistor) or (tft)) near8	USPAT;	2004/03/09 09:24
		array near8 substrate) and ((signal or gate or	US-PGPUB;	200 17 007 00 09.24
		signaling or scan\$4 or data) near3 (line or	EPO; JPO;	
		electrode)) and array and insulat\$4 and (dielectric	DERWENT;	
		near "6" constant) and (pixel near4 electrode) and	IBM_TDB	
		hole) and (silicon near3 nitride)) and ((indium adj		
		(tin or zinc) adj oxide) or ito or izo)		
-	4402	((indium adj (tin or zinc) adj oxide) or ito or izo)	USPAT;	2004/03/09 09:25
		near10 (pixel adj electrode)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

	203	(((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data) near3 (line or electrode)) and array and insulat\$4 and (dielectric near "6" constant) and (pixel near4 electrode) and hole) and (silicon near3 nitride)) and (((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 09:25
-	790203	chrom\$4 or cr	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 10:11
-	4230267	aluminum or al	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 10:12
-	150	((((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data) near3 (line or electrode)) and array and insulat\$4 and (dielectric near "6" constant) and (pixel near4 electrode) and hole) and (silicon near3 nitride)) and (((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode))) and (chrom\$4 or cr) and (aluminum or al)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 10:45
-	448074	molybdenum or mo	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 10:46
-	96476	(chrom\$4 or cr) and (aluminum or al) and (molybdenum or mo)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 10:47
-	243803	((chrom\$4 or cr) or (aluminum or al) or (molybdenum or mo)) near5 alloy	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 10:49
-	87	((((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data) near3 (line or electrode)) and array and insulat\$4 and (dielectric near "6" constant) and (pixel near4 electrode) and hole) and (silicon near3 nitride)) and (((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode))) and ((chrom\$4 or cr) and (aluminum or al) and (molybdenum or mo)) and (((chrom\$4 or cr) or (aluminum or al) or (molybdenum or mo)) near5 alloy)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 10:53
-	67	(((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data or drain or source) near3 (line or electrode)) and array and insulat\$4 and (dielectric near6 constant) and (pixel near4 electrode) and hole and passivation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:13

-	54	((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data or drain or source) near3 (line or electrode)) and array and insulat\$4 and (dielectric near6 constant) and (pixel near4 electrode) and hole and passivation) and (silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:02
	51	near3 nitride) (((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data or drain or source) near3 (line or electrode)) and array and insulat\$4 and (dielectric near6 constant) and (pixel near4 electrode) and hole and passivation) and (silicon near3 nitride)) and ((indium adj (tin or zinc) adj	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:02
-	34	oxide) or ito or izo) (((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data or drain or source) near3 (line or electrode)) and array and insulat\$4 and (dielectric near6 constant) and (pixel near4 electrode) and hole and passivation) and (silicon near3 nitride)) and (((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:04
-	33	((((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data or drain or source) near3 (line or electrode)) and array and insulat\$4 and (dielectric near6 constant) and (pixel near4 electrode) and hole and passivation) and (silicon near3 nitride)) and (((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode))) and ((chrom\$4 or cr) or (aluminum or al) or (molybdenum or mo))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:05
-	1426	349/43	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/09 11:10
-	2218	349/42	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:05
-	3078	349/43 or 349/42	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:06
-	11	(((((((thin near3 film near3 transistor) or (tft)) near8 array near8 substrate) and ((signal or gate or signaling or scan\$4 or data or drain or source) near3 (line or electrode)) and array and insulat\$4 and (dielectric near6 constant) and (pixel near4 electrode) and hole and passivation) and (silicon near3 nitride)) and (((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode))) and ((chrom\$4 or cr) or (aluminum or al) or (molyhdonum or mo))) and (349/43 or 349/43)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:10
-	358	(molybdenum or mo))) and (349/43 or 349/42) 349/51	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 11:10

		· · · · · · · · · · · · · · · · · · ·		I =
-	89	349/52	USPAT;	2004/03/09 11:10
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	3427	349/43 or 349/42 or 349/51 or 349/52	USPAT;	2004/03/09 11:11
	,		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	11	((((((thin near3 film near3 transistor) or (tft))	USPAT;	2004/03/09 11:11
		near8 array near8 substrate) and ((signal or gate	US-PGPUB;	
-		or signaling or scan\$4 or data or drain or source)	EPO; JPO;	
		near3 (line or electrode)) and array and insulat\$4	DERWENT;	
		and (dielectric near6 constant) and (pixel near4	IBM_TDB	
		electrode) and hole and passivation) and (silicon		
		near3 nitride)) and (((indium adj (tin or zinc) adj oxide) or ito or izo) near10 (pixel adj electrode)))		
		and ((chrom\$4 or cr) or (aluminum or al) or		
		(molybdenum or mo))) and (349/43 or 349/42 or		
		349/51 or 349/52)		
1 -	6754	insulat\$4 near8 (dielectric and silicon near3	USPAT;	2004/03/09 11:12
İ		nitride)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	90796	(gate or scan\$4) near8 ((chrom\$4 or cr) or	USPAT;	2004/03/09 11:14
		(aluminum or al) or (molybdenum or mo))	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM_TDB	
_	42185	((thin near3 film near3 transistor) or (tft)) and	USPAT;	2004/03/09 11:14
		substrate	US-PGPUB;	200 1, 00, 05 11:11
			EPO; JPO;	
			DERWENT;	
-			IBM_TDB	
-	706656	(drain or data or source or signal\$4) near3 (line or	USPAT;	2004/03/09 11:15
		electrode)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	718	(insulat\$4 near8 (dielectric and silicon near3	IBM_TDB USPAT;	2004/03/09 11:15
	/13	nitride)) and ((gate or scan\$4) near8 ((chrom\$4 or	US-PGPUB;	2007/03/03 11.13
		cr) or (aluminum or al) or (molybdenum or mo)))	EPO; JPO;	
		and (((thin near3 film near3 transistor) or (tft))	DERWENT;	
		and substrate) and ((drain or data or source or	IBM_TDB	
	_	signal\$4) near3 (line or electrode))		
-	32786	passivation near3 (film or layer or plate or coat\$4)	USPAT;	2004/03/09 11:16
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	290	((insulat\$4 near8 (dielectric and silicon near3	IBM_TDB USPAT;	2004/03/09 11:29
	250	nitride)) and ((gate or scan\$4) near8 ((chrom\$4 or	US-PGPUB;	2007/03/03 11.29
		cr) or (aluminum or al) or (molybdenum or mo)))	EPO; JPO;	
		and (((thin near3 film near3 transistor) or (tft))	DERWENT;	
		and substrate) and ((drain or data or source or	IBM_TDB	
		signal\$4) near3 (line or electrode))) and	_	
		(passivation near3 (film or layer or plate or		
		coat\$4))		

	7		T 772	T
-	1799	(passivation near3 (film or layer or plate or coat\$4)) same ((chemical near3 vapor near3 deposit\$3) or pevcd)	USPAT; US-PGPUB; EPO; JPO;	2004/03/09 11:31
•		deposites, or perca,	DERWENT; IBM_TDB	
-	21	((insulat\$4 near8 (dielectric and silicon near3	USPAT;	2004/03/09 11:17
		nitride)) and ((gate or scan\$4) near8 ((chrom\$4 or	US-PGPUB;	
		cr) or (aluminum or al) or (molybdenum or mo))) and (((thin near3 film near3 transistor) or (tft))	EPO; JPO; DERWENT;	
		and substrate) and ((drain or data or source or	IBM_TDB	
		signal\$4) near3 (line or electrode))) and	_	
		((passivation near3 (film or layer or plate or		
		coat\$4)) same ((chemical near3 vapor near3 deposit\$3) or pevcd))		
-	152		USPAT;	2004/03/09 11:18
		silicon near3 nitride)) and ((gate or scan\$4) near8	US-PGPUB;	200 1,00,00 11110
		((chrom\$4 or cr) or (aluminum or al) or	EPO; JPO;	
		(molybdenum or mo))) and (((thin near3 film	DERWENT;	
		near3 transistor) or (tft)) and substrate) and ((drain or data or source or signal\$4) near3 (line	IBM_TDB	
		or electrode))) and (passivation near3 (film or		
		layer or plate or coat\$4)))		
-	6	349/\$6 and (((insulat\$4 near8 (dielectric and	USPAT;	2004/03/09 11:18
		silicon near3 nitride)) and ((gate or scan\$4) near8	US-PGPUB;	
		((chrom\$4 or cr) or (aluminum or al) or (molybdenum or mo))) and (((thin near3 film	EPO; JPO; DERWENT;	
		near3 transistor) or (tft)) and substrate) and	IBM_TDB	
		((drain or data or source or signal\$4) near3 (line		
		or electrode))) and ((passivation near3 (film or		
		layer or plate or coat\$4)) same ((chemical near3		
_	138	vapor near3 deposit\$3) or pevcd))) (((insulat\$4 near8 (dielectric and silicon near3	USPAT;	2004/03/09 11:30
		nitride)) and ((gate or scan\$4) near8 ((chrom\$4 or	US-PGPUB;	200 1,03,03 11.30
		cr) or (aluminum or al) or (molybdenum or mo)))	EPO; JPO;	
		and (((thin near3 film near3 transistor) or (tft))	DERWENT;	
		and substrate) and ((drain or data or source or signal\$4) near3 (line or electrode))) and	IBM_TDB	
		(passivation near3 (film or layer or plate or		
		coat\$4))) and ((dielectric or permittiv\$4) near3		
	7.4	(constant or coefficient))		
-	74	((((insulat\$4 near8 (dielectric and silicon near3 nitride)) and ((gate or scan\$4) near8 ((chrom\$4 or	USPAT; US-PGPUB;	2004/03/09 11:30
		cr) or (aluminum or al) or (molybdenum or mo)))	EPO; JPO;	
		and (((thin near3 film near3 transistor) or (tft))	DERWENT;	
		and substrate) and ((drain or data or source or	IBM_TDB	
	1	signal\$4) near3 (line or electrode))) and		
		(passivation near3 (film or layer or plate or coat\$4))) and ((dielectric or permittiv\$4) near3		
		(constant or coefficient))) and 349/\$6		
- ,	32	(((((insulat\$4 near8 (dielectric and silicon near3	USPAT;	2004/03/10 10:57
		nitride)) and ((gate or scan\$4) near8 ((chrom\$4 or	US-PGPUB;	
]	cr) or (aluminum or al) or (molybdenum or mo))) and (((thin near3 film near3 transistor) or (tft))	EPO; JPO; DERWENT;	
		and substrate) and ((drain or data or source or	IBM_TDB	
		signal\$4) near3 (line or electrode))) and		
	Ŧ I	(passivation near3 (film or layer or plate or		
		coat\$4))) and ((dielectric or permittiv\$4) near3 (constant or coefficient))) and 349/\$6) and		
		((chemical near3 vapor near3 deposit\$3) or pevcd)		
	·	,, or portou		